

AMENDMENTS TO THE SPECIFICATION:

Please amend Page 1, lines 26-33 to read as follows:

--In the case of metallization, the choice of the new wiring material is reasonably straight forward, but the choice of the intermetal dielectric (IMD) is not as clear. Many new low-k dielectrics which are based on organic or glass materials have become recently available to the semiconductor industry; See, for example, co-assigned U.S. application Serial No. 09/360,738 (~~Attorney docket~~
~~YOR91999074US1~~); co-assigned U.S. application Serial No. 09/361,396 (~~Attorney~~
~~Docket YOR91999075US1~~) U.S. Patent No. 6,440,560 to Gates, et al.; U.S. Patent No. 5,393,712 to Rostoker, et al; U.S. Patent No. 5,470,801 to Kapoor, et al.; and U.S. Patent No. 5,598,026 to Kapoor, et al.--